

Important notice

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Should be replaced with:

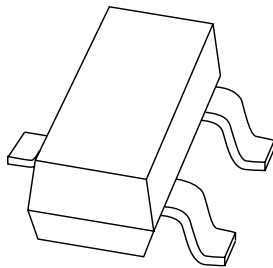
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



BFS19

NPN medium frequency transistor

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 05

NPN medium frequency transistor

BFS19

FEATURES

- $I_{C(max)} = 25 \text{ mA}$
- $V_{CEO(max)} = 20 \text{ V}$.

APPLICATIONS

- Medium frequency applications in thick and thin-film circuits.

DESCRIPTION

NPN medium frequency transistor in a SOT23 plastic package.

MARKING

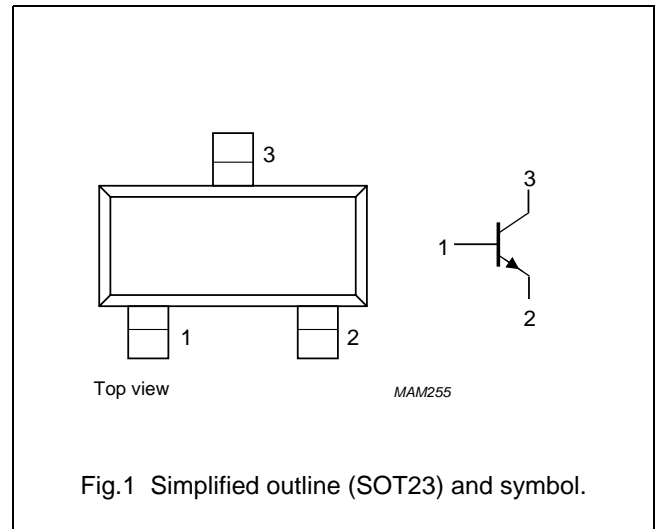
TYPE NUMBER	MARKING CODE ⁽¹⁾
BFS19	F2*

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BFS19	–	plastic surface mounted package; 3 leads	SOT23

NPN medium frequency transistor

BFS19

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	30	V
V _{CEO}	collector-emitter voltage	open base	–	20	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	30	mA
I _{CM}	peak collector current		–	30	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN medium frequency transistor

BFS19

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	65	–	225	
V_{BE}	base-emitter voltage	$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	650	–	740	mV
C_c	collector capacitance	$I_E = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	1	–	pF
C_{re}	feedback capacitance	$I_C = 0\text{ mA}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	0.85	–	pF
f_T	transition frequency	$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	–	260	–	MHz

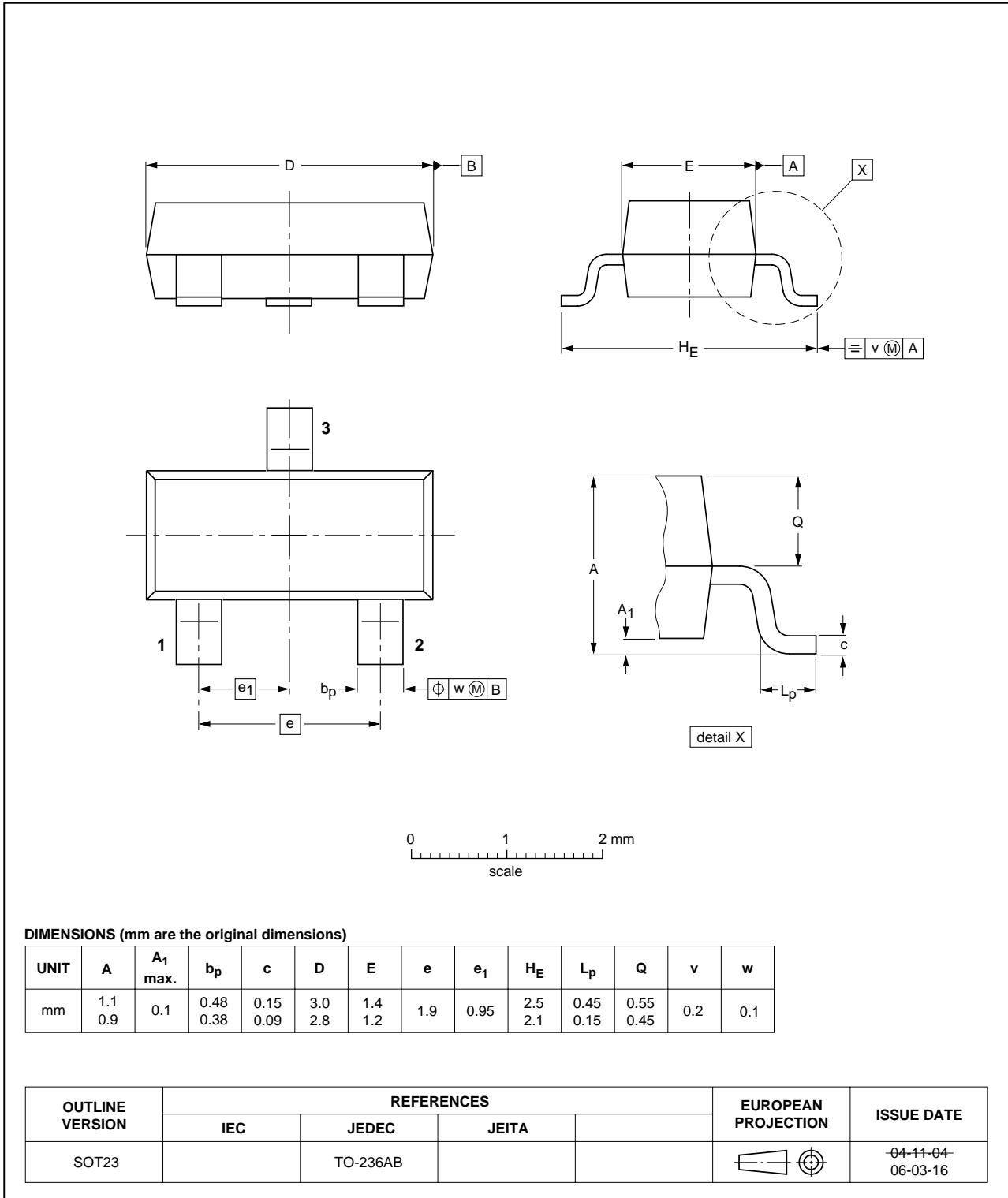
NPN medium frequency transistor

BFS19

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN medium frequency transistor

BFS19

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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